## SN74CBTD3384C 10-BIT FET BUS SWITCH WITH LEVEL SHIFTING 5-V BUS SWITCH WITH –2-V UNDERSHOOT PROTECTION

SCDS133A -SEPTEMBER 2003 - REVISED OCTOBER 2003

- Undershoot Protection for Off-Isolation on A and B Ports Up To -2 V
- Integrated Diode to V<sub>CC</sub> Provides 5-V Input Down To 3.3-V Output Level Shift
- Bidirectional Data Flow, With Near-Zero Propagation Delay
- Low ON-State Resistance (r<sub>on</sub>)
   Characteristics (r<sub>on</sub> = 3 Ω Typical)
- Low Input/Output Capacitance Minimizes Loading and Signal Distortion (C<sub>io(OFF)</sub> = 5 pF Typical)
- Data and Control Inputs Provide Undershoot Clamp Diodes
- V<sub>CC</sub> Operating Range From 4.5 V to 5.5 V

- Data I/Os Support 0 to 5-V Signaling Levels (0.8-V, 1.2-V, 1.5-V, 1.8-V, 2.5-V, 3.3-V, 5-V)
- Control Inputs Can be Driven by TTL or 5-V/3.3-V CMOS Outputs
- I<sub>off</sub> Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
  - 2000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)
- Supports Both Digital and Analog Applications: Memory Interleaving, Bus Isolation, Low-Distortion Signal Gating

# DB, DBQ, DGV, DW, OR PW PACKAGE (TOP VIEW)

			_	
10E [	1	$\cup_{24}$	1	V <sub>CC</sub>
1B1 [	2	23	1	2B5
1A1 [	3	22	1	2A5
1A2[	4	21		2A4
1B2 [	5	20	1	2B4
1B3 [	6	19	1	2B3
1A3 [	7	18	1	2A3
1A4 [	8	17	•	2A2
1B4 [	9	16	: [	2B2
1B5 [	10	15	: [	2B1
1A5 [	11	14		2A1
GND [	12	13		2 <mark>OE</mark>

#### description/ordering information

## ORDERING INFORMATION

TA	PACKAGI	<u>=</u> †	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	COIC DW	Tube	SN74CBTD3384CDW	CDTD2204C
	SOIC - DW	Tape and reel	SN74CBTD3384CDWR	CBTD3384C
	CCOD DD	Tube	SN74CBTD3384CDB	000040
-40°C to 85°C	SSOP – DB	Tape and reel	SN74CBTD3384CDBR	CC384C
-40 C to 65 C	SSOP (QSOP) – DBQ	Tape and reel	SN74CBTD3384CDBQR	CBTD3384C
	TOOOD DW	Tube	SN74CBTD3384CPW	000040
	TSSOP - PW	Tape and reel	SN74CBTD3384CPWR	CC384C
	TVSOP - DGV	Tape and reel	SN74CBTD3384CDGVR	CC384C

<sup>†</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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SCDS133A -SEPTEMBER 2003 - REVISED OCTOBER 2003

#### description/ordering information (continued)

The SN74CBTD3384C is a high-speed TTL-compatible FET bus switch with low ON-state resistance (ron), allowing for minimal propagation delay. This device features an integrated diode in series with V<sub>CC</sub> to provide level shifting for 5-V input down to 3.3-V output levels. Active Undershoot-Protection Circuitry on the A and B ports of the SN74CBTD3384C provides protection for undershoot up to -2 V by sensing an undershoot event and ensuring that the switch remains in the proper OFF state.

The SN74CBTD3384C is organized as two 5-bit bus switches with separate output-enable (1OE, 2OE) inputs. It can be used as two 5-bit bus switches or as one 10-bit bus switch. When  $\overline{OE}$  is low, the associated 5-bit bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When OE is high, the associated 5-bit bus switch is OFF, and a high-impedance state exists between the A and B ports.

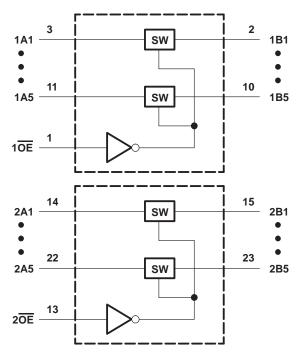
This device is fully specified for partial-power-down applications using Ioff. The Ioff feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down,  $\overline{\text{OE}}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

**FUNCTION TABLE** (each 5-bit bus switch)

INPUT OE	INPUT/OUTPUT A	FUNCTION
L	В	A port = B port
Н	Z	Disconnect

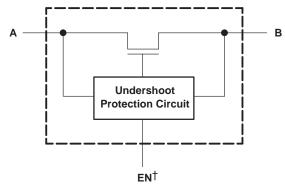
## logic diagram (positive logic)





SCDS133A -SEPTEMBER 2003 - REVISED OCTOBER 2003

## simplified schematic, each FET switch (SW)



†EN is the internal enable signal applied to the switch.

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V <sub>CC</sub>		–0.5 V to 7 V
Control input voltage range, VIN (see Notes 1 a	and 2)	0.5 V to 7 V
Switch I/O voltage range, V <sub>I/O</sub> (see Notes 1, 2,	and 3)	0.5 V to 7 V
Control input clamp current, I <sub>IK</sub> (V <sub>IN</sub> < 0)		–50 mA
I/O port clamp current, $I_{I/OK}$ ( $V_{I/O} < 0$ )		–50 mA
ON-state switch current, I <sub>I/O</sub> (see Note 4)		±128 mA
Continuous current through V <sub>CC</sub> or GND termin		
Package thermal impedance, θ <sub>JA</sub> (see Note 5)	: DB package	63°C/W
	DBQ package	61°C/W
	DGV package	86°C/W
	DW package	46°C/W
	PW package	88°C/W
Storage temperature range, Teta		-65°C to 150°C

<sup>‡</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltages are with respect to ground unless otherwise specified.
  - 2. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
  - 3.  $V_I$  and  $V_O$  are used to denote specific conditions for  $V_{I/O}$ .
  - 4.  $I_I$  and  $I_O$  are used to denote specific conditions for  $I_{I/O}$ .
  - 5. The package thermal impedance is calculated in accordance with JESD 51-7.

### recommended operating conditions (see Notes 6 and 7)

		MIN	MAX	UNIT
Vcc	Supply voltage	4.5	5.5	V
VIH	High-level control input voltage	2	5.5	V
VIL	Low-level control input voltage	0	8.0	V
V <sub>I/O</sub>	Data input/output voltage	0	5.5	V
TA	Operating free-air temperature	-40	85	°C

- NOTES: 6. All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.
  - 7. In applications with fast edge rates, multiple outputs switching, and operating at high frequencies, the output may have little or no level-shifting effect.



## SN74CBTD3384C 10-BIT FET BUS SWITCH WITH LEVEL SHIFTING 5-V BUS SWITCH WITH –2-V UNDERSHOOT PROTECTION

SCDS133A -SEPTEMBER 2003 - REVISED OCTOBER 2003

# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PAR	AMETER		TEST CONDITIO	NS	MIN	TYP†	MAX	UNIT
VIK	Control inputs	V <sub>CC</sub> = 4.5 V,	$I_{IN} = -18 \text{ mA}$				-1.8	V
VIKU	Data inputs	V <sub>CC</sub> = 5 V,	$0 \text{ mA} > I_I \ge -50 \text{ mA},$ $V_{IN} = V_{CC} \text{ or GND},$	Switch OFF			-2	V
VOH		See Figures 4 and 5						
I <sub>IN</sub>	Control inputs	V <sub>CC</sub> = 5.5 V,	$V_{IN} = V_{CC}$ or GND				±1	μΑ
loz‡		V <sub>CC</sub> = 5.5 V,	$V_O = 0 \text{ to } 5.5 \text{ V},$ $V_I = 0,$	Switch OFF, V <sub>IN</sub> = V <sub>CC</sub> or GND			±10	μА
l <sub>off</sub>		$V_{CC} = 0$ ,	$V_0 = 0 \text{ to } 5.5 \text{ V},$	V <sub>I</sub> = 0			10	μΑ
Icc		V <sub>CC</sub> = 5.5 V,	$I_{I/O} = 0,$ $V_{IN} = V_{CC}$ or GND,	Switch ON or OFF			1.5	mA
∆lcc§	Control inputs	V <sub>CC</sub> = 5.5 V,	One input at 3.4 V,	Other inputs at V <sub>CC</sub> or GND			2.5	mA
C <sub>in</sub>	Control inputs	$V_{IN} = 3 \text{ V or } 0$				3.5		pF
C <sub>io(OFF)</sub>		$V_{I/O} = 3 \text{ V or } 0,$	Switch OFF,	$V_{IN} = V_{CC}$ or GND		5		pF
C <sub>io(ON)</sub>		$V_{I/O} = 3 \text{ V or } 0,$	Switch ON,	V <sub>IN</sub> = V <sub>CC</sub> or GND		12.5		pF
			V 0	I <sub>O</sub> = 64 mA		3	6	
$r_{on}\P$		V <sub>CC</sub> = 4.5 V	V <sub>I</sub> = 0	I <sub>O</sub> = 30 mA		3	6	Ω
			V <sub>I</sub> = 2.4 V,	$I_O = -15 \text{ mA}$		8	20	

VIN and IIN refer to control inputs. VI, VO, II, and IO refer to data pins.

# switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM	TO	ΥCC =	UNIT	
	(INPUT)	(OUTPUT)	MIN	MAX	
t <sub>pd</sub> #	A or B	B or A		0.15	ns
t <sub>en</sub>	ŌĒ	A or B	1.5	4.8	ns
<sup>t</sup> dis	ŌĒ	A or B	1.5	4.8	ns

<sup>#</sup>The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).



<sup>†</sup> All typical values are at  $V_{CC}$  = 5 V (unless otherwise noted),  $T_A$  = 25°C.

<sup>‡</sup> For I/O ports, the parameter IOZ includes the input leakage current.

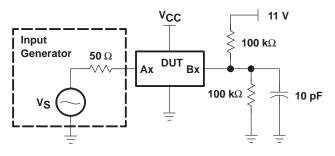
<sup>§</sup> This is the increase in supply current for each input that is at the specified voltage level, rather than VCC or GND.

<sup>¶</sup> Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

## undershoot characteristics (see Figures 1 and 2)

PARAMETER		TEST CONDI	TIONS	MIN	TYP†	MAX	UNIT
VOUTU	$V_{CC} = 5.5 \text{ V},$	Switch OFF,	$V_{IN} = V_{CC}$ or GND	2	V <sub>OH</sub> -0.3		V

 $<sup>\</sup>dagger$  All typical values are at V<sub>CC</sub> = 5 V (unless otherwise noted), T<sub>A</sub> = 25°C.





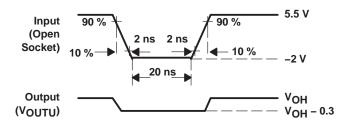
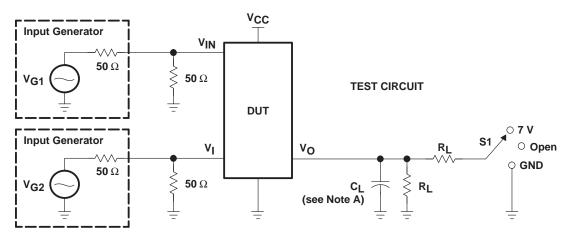


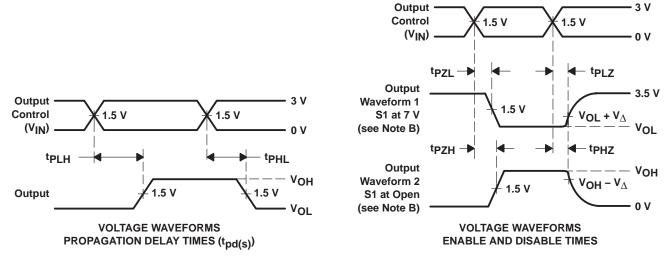
Figure 2. Transient Input Voltage (V<sub>I</sub>) and Output Voltage (V<sub>OUTU</sub>) Waveforms (Switch OFF)

SCDS133A -SEPTEMBER 2003 - REVISED OCTOBER 2003

#### PARAMETER MEASUREMENT INFORMATION FOR LEVEL SHIFTER



TEST	VCC	S1	RL	٧ <sub>I</sub>	CL	${f v}_{\!\Delta}$
tpd(s)	5 V $\pm$ 0.5 V	Open	500 Ω	V <sub>CC</sub> or GND	50 pF	
tPLZ/tPZL	5 V ± 0.5 V	7 V	500 Ω	GND	50 pF	0.3 V
t <sub>PHZ</sub> /t <sub>PZH</sub>	5 V ± 0.5 V	Open	500 Ω	VCC	50 pF	0.3 V



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

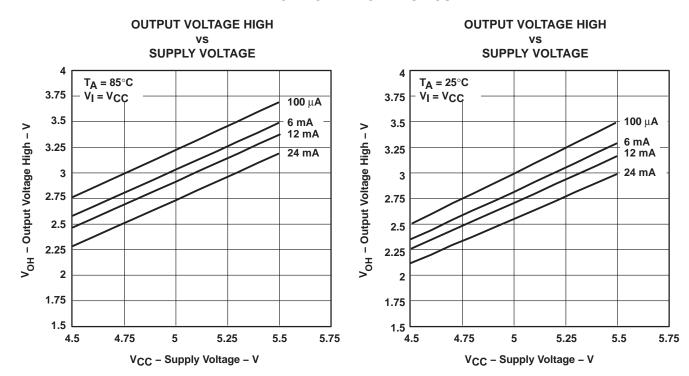
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_{O} = 50 \Omega$ ,  $t_{f} \leq$  2.5 ns,  $t_{f} \leq$  2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G.  $tp_{LH}$  and  $tp_{HL}$  are the same as  $tp_{d(s)}$ . The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Test Circuit and Voltage Waveforms



SCDS133A -SEPTEMBER 2003 - REVISED OCTOBER 2003

#### **TYPICAL CHARACTERISTICS**



#### OUTPUT VOLTAGE HIGH vs SUPPLY VOLTAGE

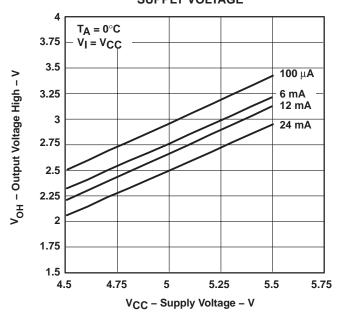


Figure 4. V<sub>OH</sub> Values

## **TYPICAL CHARACTERISTICS (continued)**

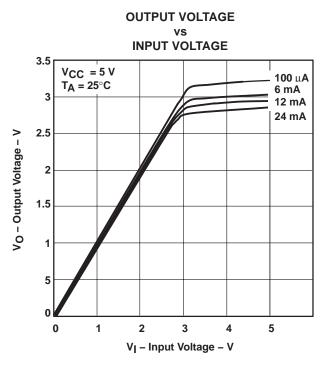


Figure 5. Data Output Voltage vs Data Input Voltage



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#### **PACKAGING INFORMATION**

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
740DTD22040D0\/DE4	A =45 =	Duadication	TV(COD (DOV)   04	2000 H ADOF TOD	V	(4)	(5)	40 to 05	000040
74CBTD3384CDGVRE4	Active	Production	TVSOP (DGV)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C
74CBTD3384CDGVRG4	Active	Production	TVSOP (DGV)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C
SN74CBTD3384CDBQR	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CBTD3384C
SN74CBTD3384CDBQR.B	Active	Production	SSOP (DBQ)   24	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CBTD3384C
SN74CBTD3384CDBR	Active	Production	SSOP (DB)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C
SN74CBTD3384CDBR.B	Active	Production	SSOP (DB)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C
SN74CBTD3384CDGVR	Active	Production	TVSOP (DGV)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C
SN74CBTD3384CDGVR.B	Active	Production	TVSOP (DGV)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C
SN74CBTD3384CDW	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTD3384C
SN74CBTD3384CDW.B	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTD3384C
SN74CBTD3384CDWR	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	CBTD3384C
SN74CBTD3384CDWR.B	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTD3384C
SN74CBTD3384CDWRG4	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTD3384C
SN74CBTD3384CDWRG4.B	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTD3384C
SN74CBTD3384CPW	Active	Production	TSSOP (PW)   24	60   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C
SN74CBTD3384CPW.B	Active	Production	TSSOP (PW)   24	60   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C
SN74CBTD3384CPWR	Active	Production	TSSOP (PW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C
SN74CBTD3384CPWR.B	Active	Production	TSSOP (PW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C
SN74CBTD3384CPWRE4	Active	Production	TSSOP (PW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



## PACKAGE OPTION ADDENDUM

www.ti.com 23-May-2025

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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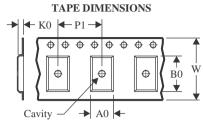
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

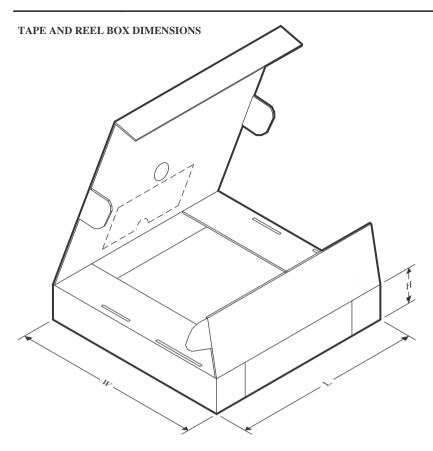


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CBTD3384CDBQR	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74CBTD3384CDBR	SSOP	DB	24	2000	330.0	16.4	8.2	8.8	2.5	12.0	16.0	Q1
SN74CBTD3384CDGVR	TVSOP	DGV	24	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTD3384CDWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74CBTD3384CDWRG4	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1



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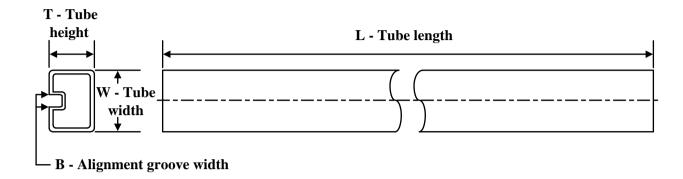
#### \*All dimensions are nominal

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Device	Package Type	Package Drawing	ng Pins SPQ Length (mr		Length (mm)	Width (mm)	Height (mm)					
SN74CBTD3384CDBQR	SSOP	DBQ	24	2500	353.0	353.0	32.0					
SN74CBTD3384CDBR	SSOP	DB	24	2000	353.0	353.0	32.0					
SN74CBTD3384CDGVR	TVSOP	DGV	24	2000	353.0	353.0	32.0					
SN74CBTD3384CDWR	SOIC	DW	24	2000	350.0	350.0	43.0					
SN74CBTD3384CDWRG4	SOIC	DW	24	2000	350.0	350.0	43.0					

# **PACKAGE MATERIALS INFORMATION**

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### **TUBE**

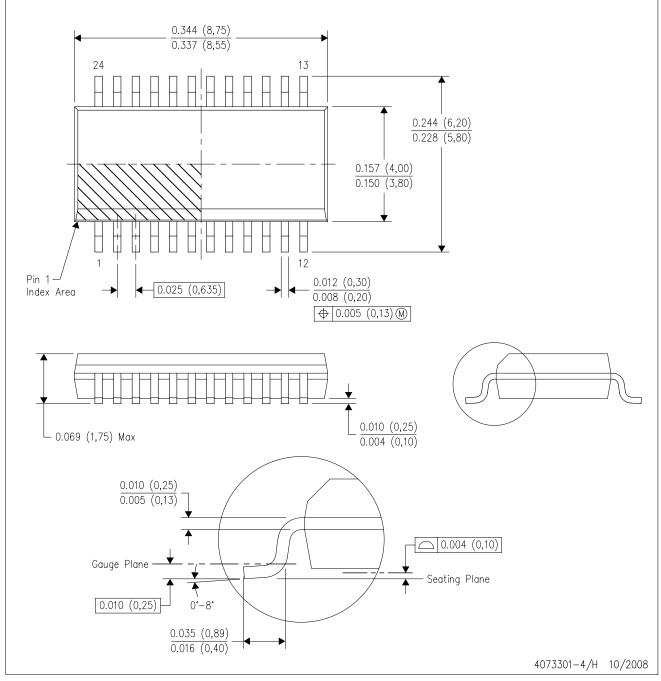


\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74CBTD3384CDW	DW	SOIC	24	25	506.98	12.7	4826	6.6
SN74CBTD3384CDW.B	DW	SOIC	24	25	506.98	12.7	4826	6.6
SN74CBTD3384CPW	PW	TSSOP	24	60	530	10.2	3600	3.5
SN74CBTD3384CPW.B	PW	TSSOP	24	60	530	10.2	3600	3.5

DBQ (R-PDSO-G24)

## PLASTIC SMALL-OUTLINE PACKAGE

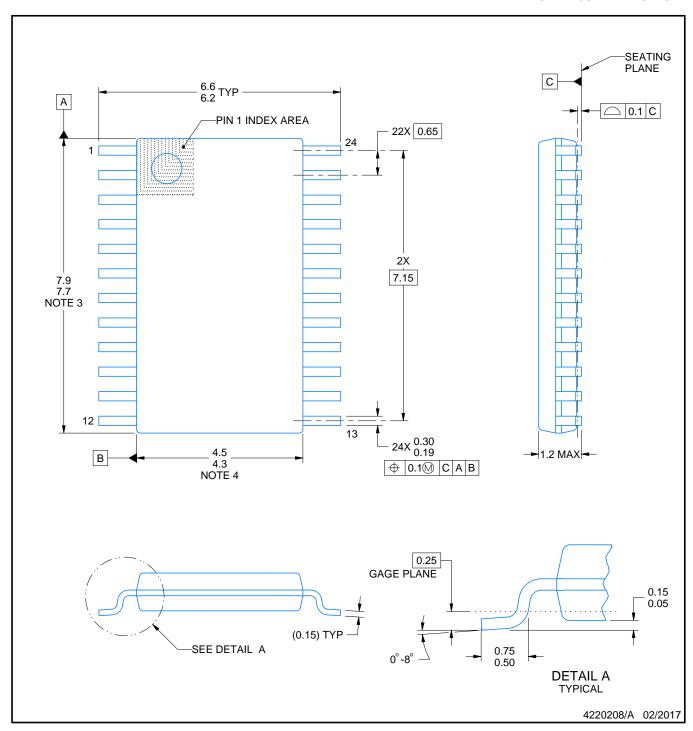


NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
- D. Falls within JEDEC MO-137 variation AE.







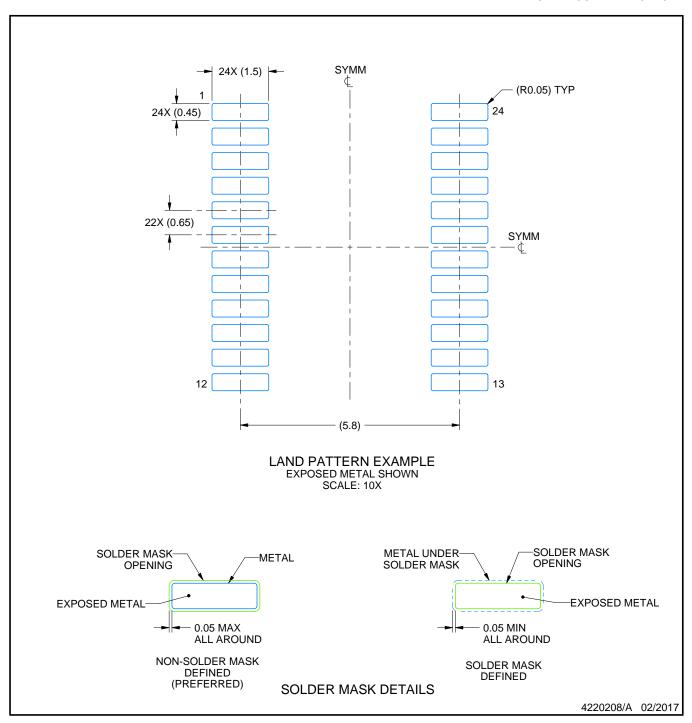
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



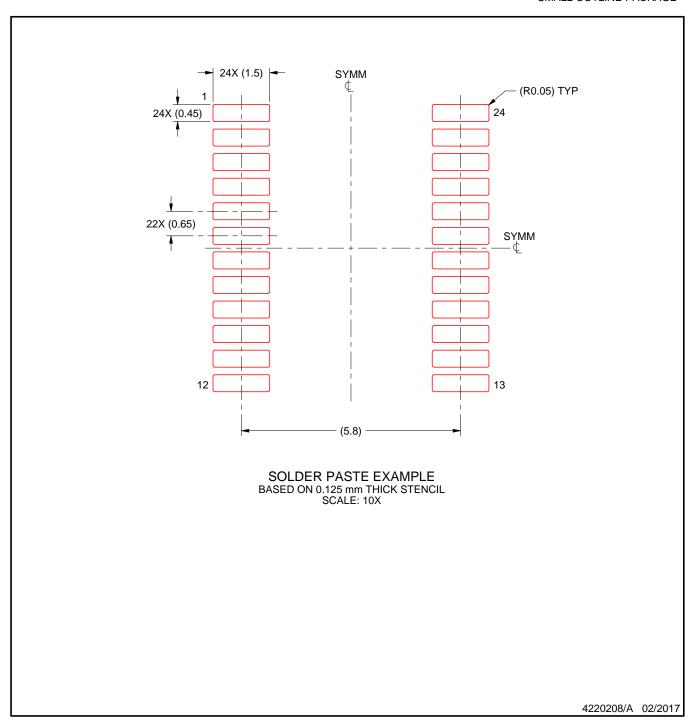


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





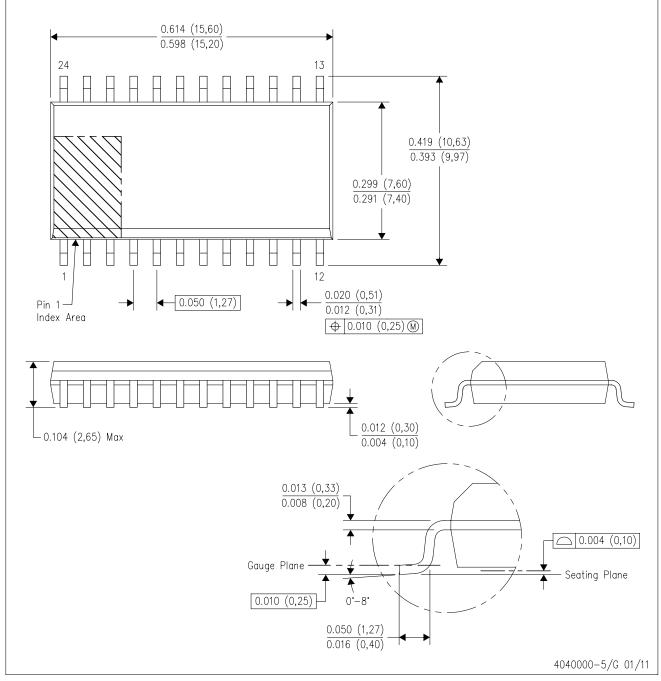
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DW (R-PDSO-G24)

## PLASTIC SMALL OUTLINE



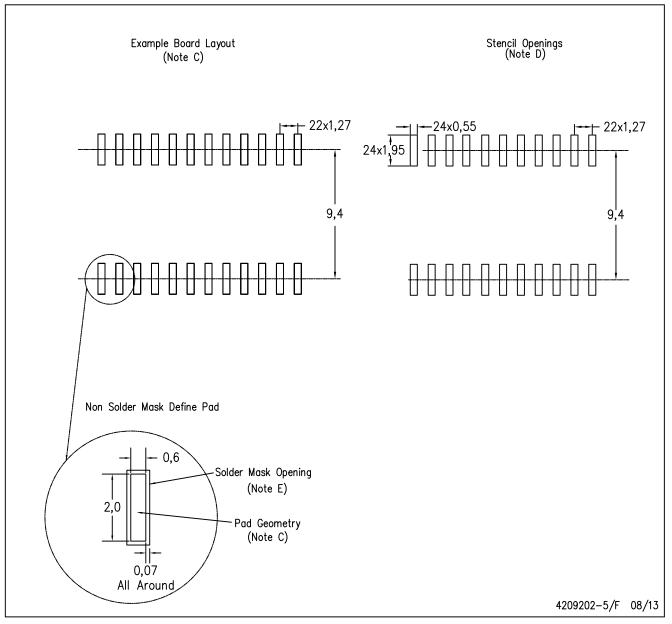
NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AD.



DW (R-PDSO-G24)

PLASTIC SMALL OUTLINE

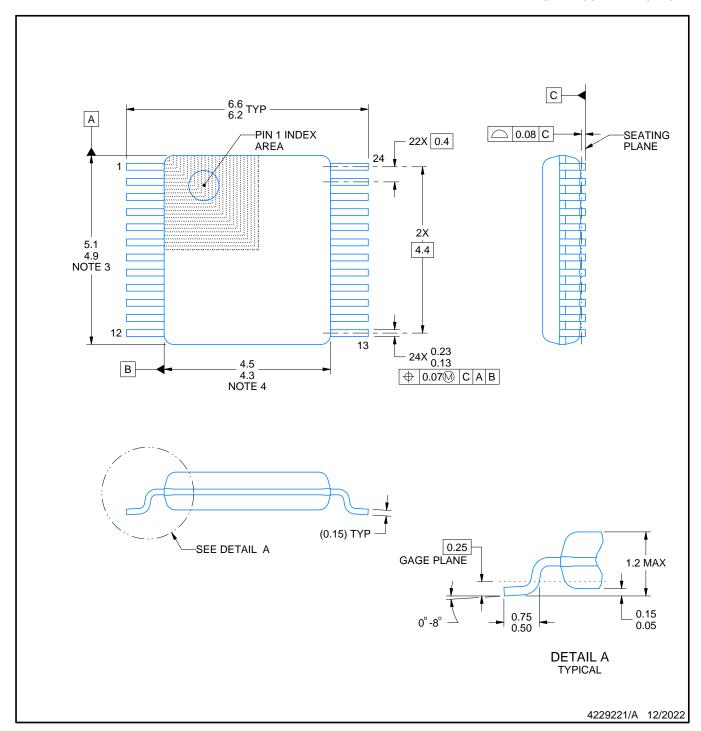


NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.







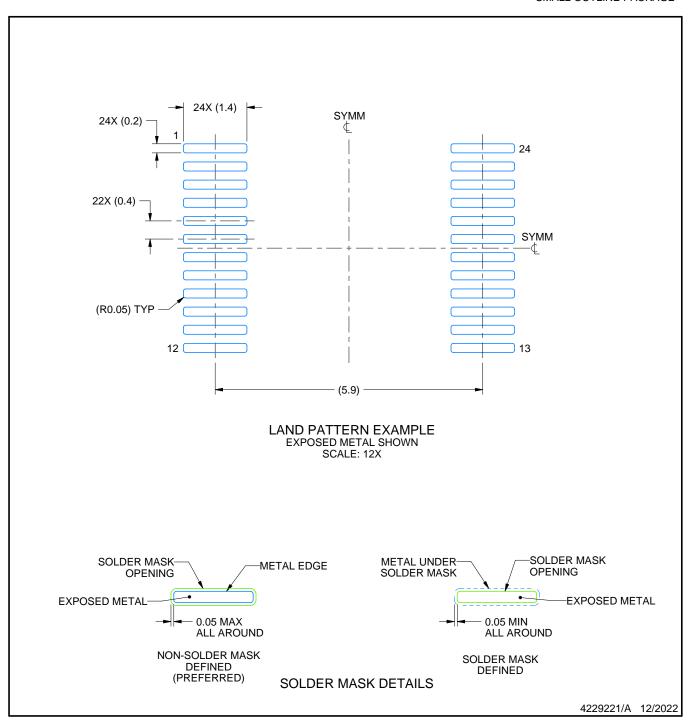
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



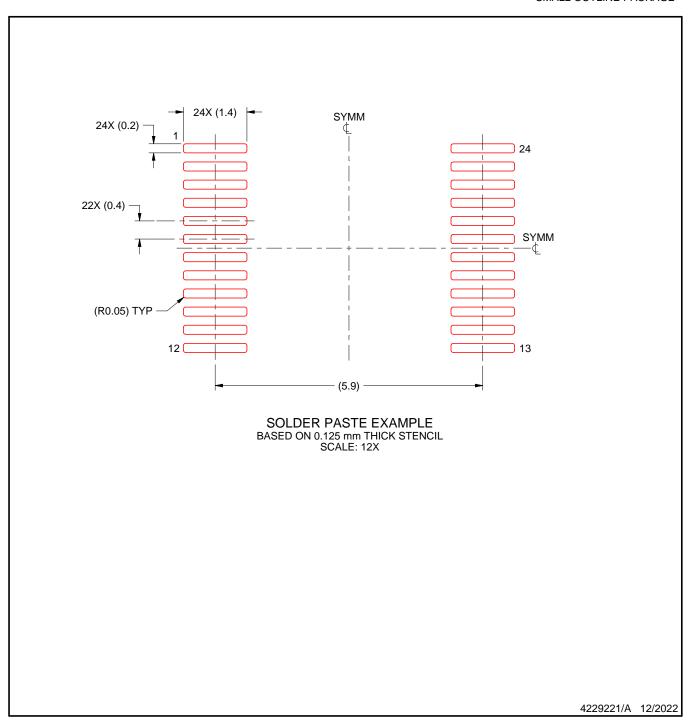


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

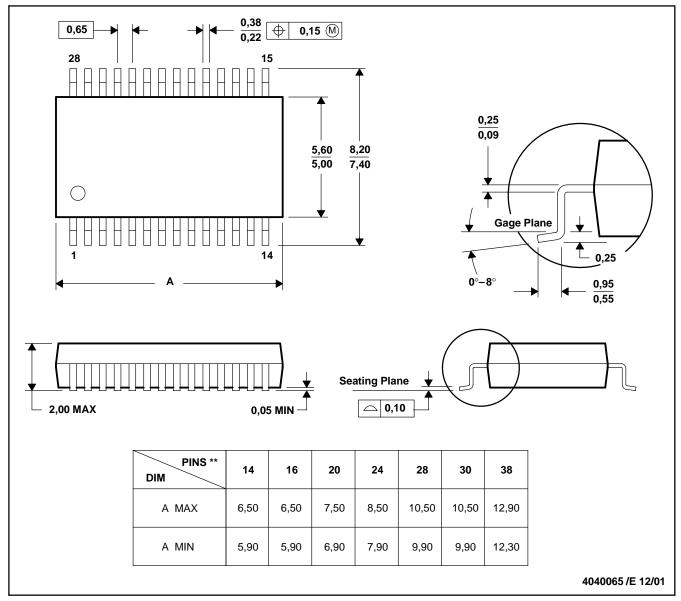
- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



## DB (R-PDSO-G\*\*)

## PLASTIC SMALL-OUTLINE

#### **28 PINS SHOWN**



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150

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